

HL6364DG



### Description

This 642 nm, 60 mW TO packaged laser diode is a compact light source that outputs a single transverse mode and is suited for a variety of applications, such as a laser level, laser scanner, or a light source for optical equipment. It is packaged in a standard Ø5.6 mm TO can package and has an A pin configuration. This laser diode is compatible with our line of laser diode and TEC controllers as well as our selection of collimation solutions and TO can laser diode mounts.

### Specifications

Absolute Maximum Ratings <sup>a</sup>	
Specification	Maximum
Optical Output Power, CW	65 mW
LD Reverse Voltage	2 V
PD Reverse Voltage	30 V
Operating Temperature	-10 °C to 50 °C
Storage Temperature	-40 °C to 85 °C

- a. Absolute Maximum Rating specifications should never be exceeded. Operating at or beyond these conditions can permanently damage the laser.



HL6364DG Specifications <sup>a</sup>				
	Symbol	Min	Typical	Max
Center Wavelength @ P <sub>op</sub>	$\lambda_o$	635 nm	642 nm	645 nm
Output Power, CW	P <sub>op</sub>	-	60 mW	-
Threshold Current	I <sub>TH</sub>	-	60 mA	80 mA
Operating Current, CW @ P <sub>op</sub>	I <sub>op</sub>	-	120 mA	155 mA
Operating Voltage @ P <sub>op</sub>	V <sub>op</sub>	-	2.5 V	3.0 V
Slope Efficiency	$\eta$	-	1.0 mW/mA	-
Beam Divergence (FWHM) @ P <sub>op</sub>	Parallel	$\theta_{//}$	7°	10°
	Perpendicular	$\theta_{\perp}$	16°	21°
Monitor Current @ P <sub>op</sub>	I <sub>PD</sub>	0.2 mA	0.35 mA	0.8 mA

- a. T<sub>CASE</sub> = 25 °C if not specified.

## Drawing

